

1035 MP 35 Watt, 50 Volts, Class C Avionics 1025 - 1150 MHz

The 1035 M pulsed syst thin-film m input prem	RAL DESCRIPTION MP is a COMMON BASE bipolar transi tems in the frequency band 1025-1150 M netallization for proven highest MTTF. 7 atch for broadband capability. Low ther nction temperature, extends life.	IHz. The device has gold The transistor includes	CASE OUTLINE 55FU, STYLE 1
Maximum	LUTE MAXIMUM RAT Power Dissipation @ 25°C ²	TINGS 125 Watts Pk	
	Voltage and Current		
BVces	Collector to Emitter Voltage	65 Volts	
BVebo	Emitter to Base Voltage	3.5 Volts	
Ic	Collector Current	2.5 Amps Pk	
Maximum	Temperatures		
-	mperature	$-65 \text{ to} + 150^{\circ}\text{C}$	
Storage Te			

ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg ηc VSWR	Power Out Power Input Power Gain Efficiency Load Mismatch Tolerance	F= 1025-1150 MHz Vcc = 50 Volts PW = 10 µsec DF = 1% F = 1090 MHz	35 10	10.5 45	3.5 10:1	Watts Watts dB %

BVeboEmitter to Base BreakdownBVcesCollector to Emitter BreakdownHfeDC Current Gain to EmitterCobOutput Capacitanceθjc²Thermal Resistance	Dwn $Ic = 15mA$	3.5 65 20	17	20 1.4	Volts Volts pF °C/W	
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Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

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